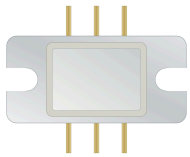
2500–3700 MHz GaN Packaged Power Amplifier — PSAT 41 dBm (typical)

LCI-PA-2500-3700-PS41T · 2500–3700 MHz · GaN Packaged Power Amplifier.



The RF table specifies: PSAT 41 dBm (typical); Power gain 22 dB (typical); PAE 47 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; PW = 100 µs; D = 10%.

CMW010B

Apply gate bias before drain bias. Remove drain bias before gate bias.

Vg: C = 10 µF

NC: 1, 6

RFin: 2

Vg: 3

Vd: 4

RFout: 5

Package outline dimensions: 18.03 × 8.7 mm.

RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; PW = 100 µs; D = 10%

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	2500	-	3700	MHz
Saturated output power	-	40.5	41	-	dBm
Power gain	-	21.5	22	-	dB
Power-added efficiency	-	42	47	-	%
Power-gain flatness	-	-	-	1	dB
Small-signal gain	-	30	31	32	dB
Small-signal gain flatness	-	-	-	±1	dB
Input VSWR	-	-	1.8	2	-

DC bias and current

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Drain voltage	-	-	-	-	28	V
Gate voltage	-	-	-	-	-2.8	V
Quiescent current	-	-	-	-	0.1 (Vd = 28 V)	A

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	-	-	-	32	V
Minimum gate bias	-	-5	-	-	V
Storage temperature	-	-65	-	150	°C
Maximum input power	-	-	-	23	dBm
Maximum channel temperature	-	-	-	200	°C

Package outline dimensions

Parameter	Value	Unit
Package outline dimensions	18.03 × 8.7	mm
Terminal span	14.7	mm

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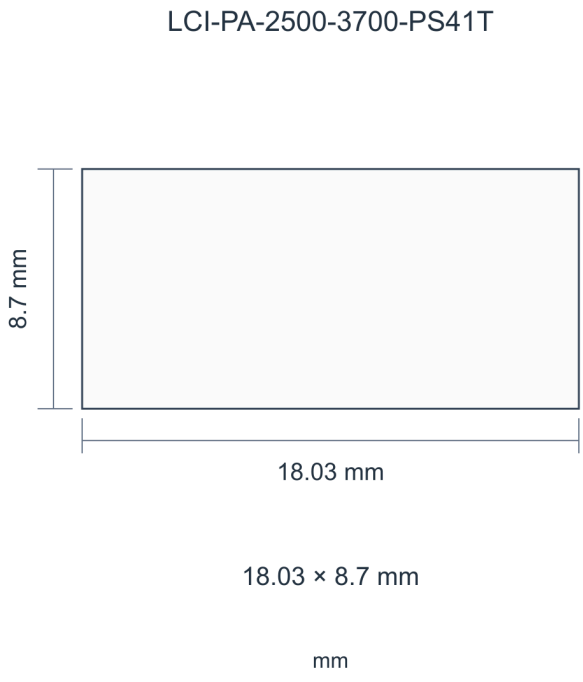
Integration notes

CMW010B Apply gate bias before drain bias. Remove drain bias before gate bias. Vg: C = 10 µF NC: 1, 6 RFin: 2 Vg: 3 Vd: 4 RFout: 5 NC (1, 6): Not connected; may be left floating or grounded

Mechanical Outline

Partial drawing showing confirmed dimensions in mm. Use the complete installation drawing for installation.

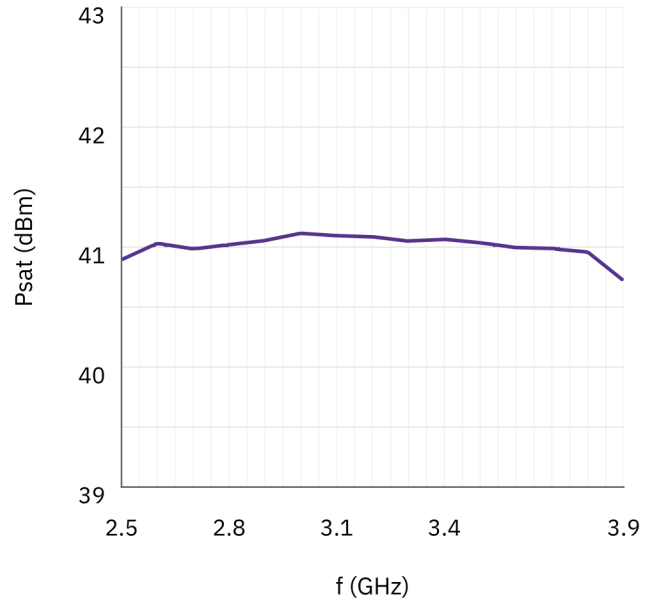


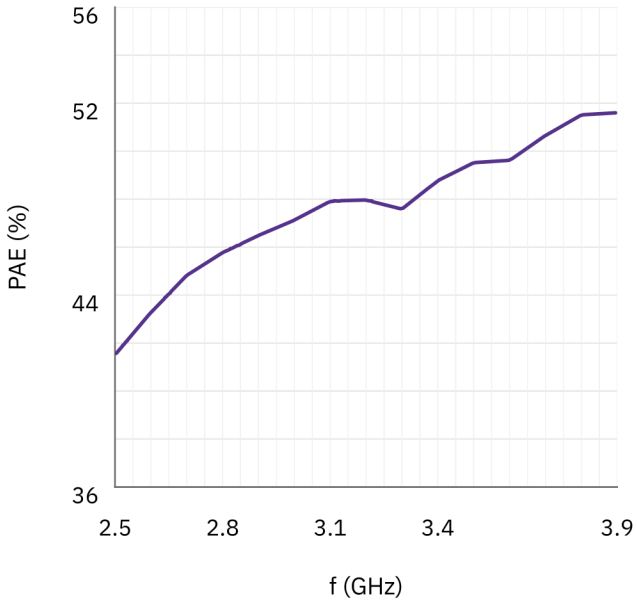
Performance curves

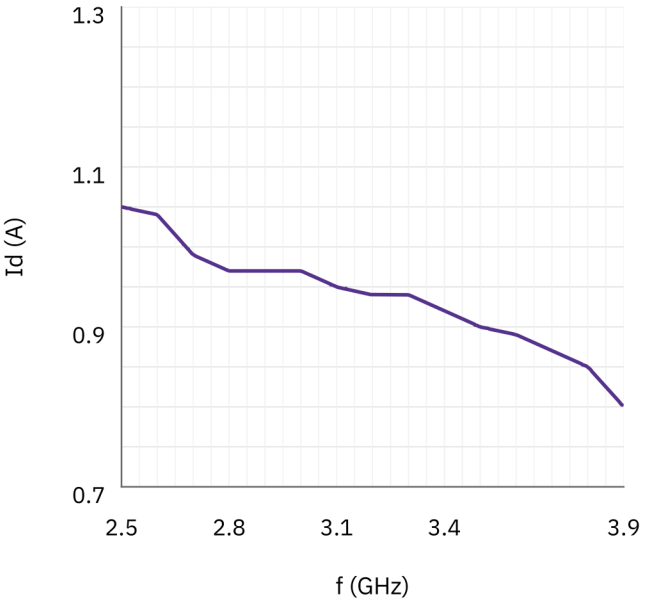
Each performance plot applies to its stated operating conditions.

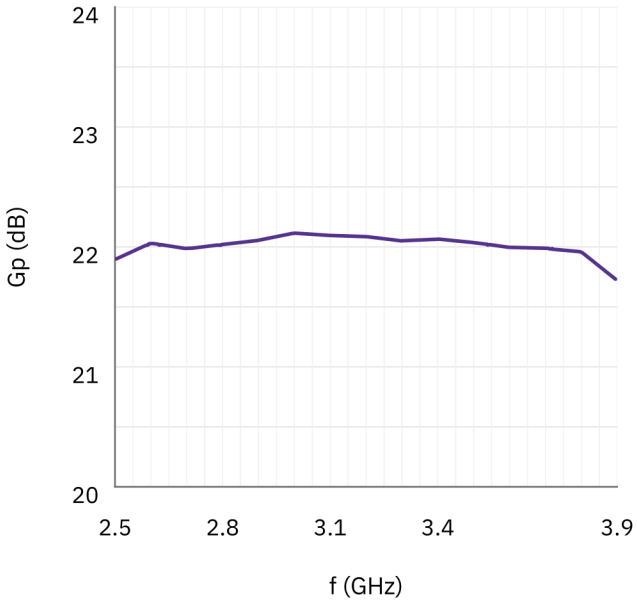
Pulsed — Saturated output power; Dynamic drain current; Power-added efficiency; Power gain.

Figure notes: TA=+25°C; Vd=+28V; Vg=-2.8V; Pin=19dBm. Readings are approximate. τ = 100 µs; D = 10%.



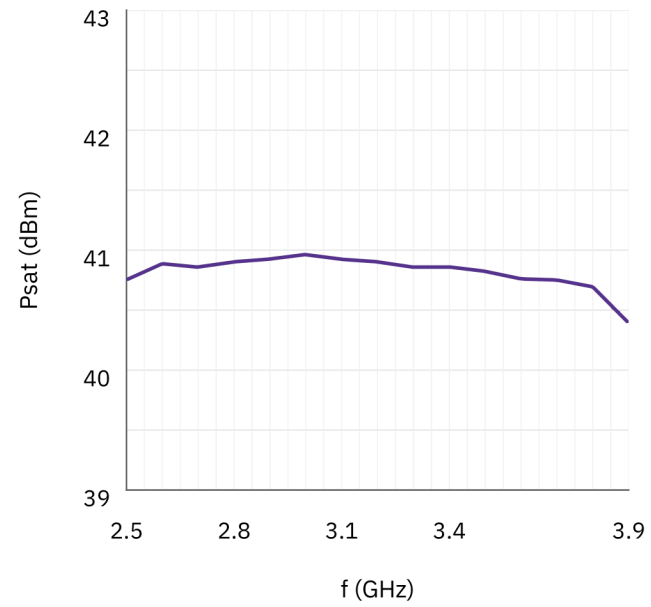


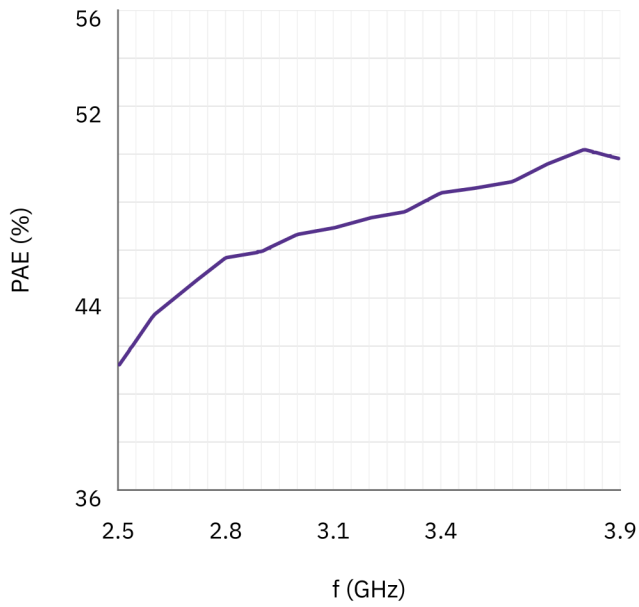


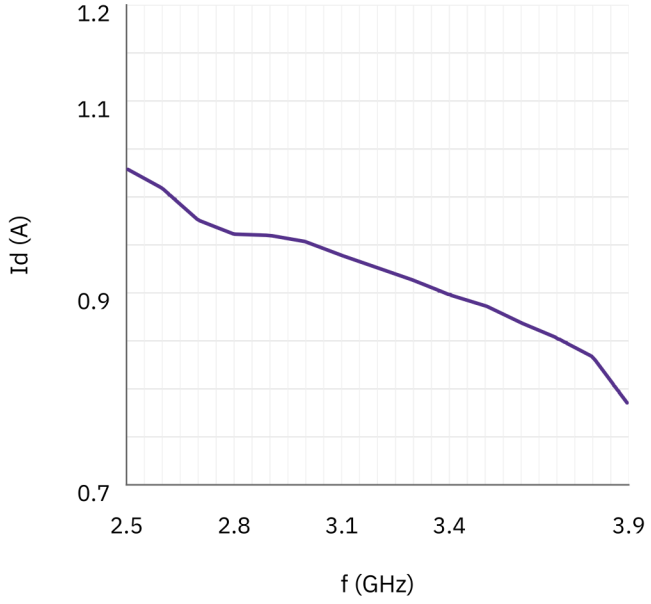


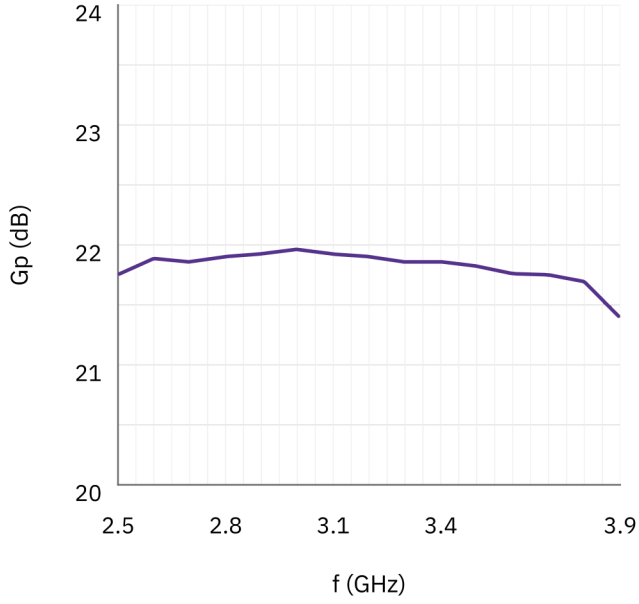
Continuous wave (CW) — Saturated output power; Dynamic drain current; Power-added efficiency; Power gain.

Figure notes: TA=+25°C; Vd=+28V; Vg=-2.8V; Pin=19dBm. Readings are approximate.









Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.